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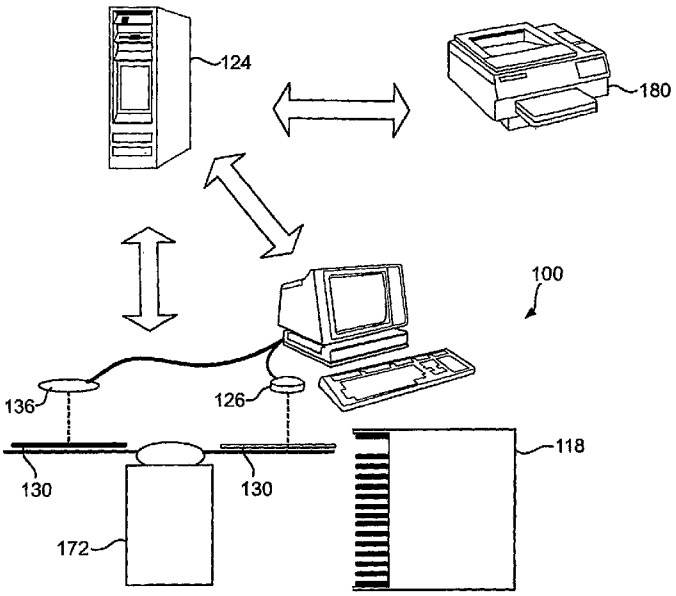
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(54) **Title:** RECLAIMING SUBSTRATES HAVING DEFECTS AND CONTAMINANTS



(57) **Abstract:** Test substrates used to test semiconductor fabrication tools are reclaimed by reading from a database the process steps performed on each test substrate and selecting a reclamation process from a plurality of reclamation processes. The reclamation process can include crystal lattice defect or metallic contaminant reduction treatments for reclaiming each test substrate. Each test substrate is sorted and placed into a group of test substrates having a common defect or contaminant reduction treatment assigned to the test substrates of the group. Additional features are described and claimed.

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